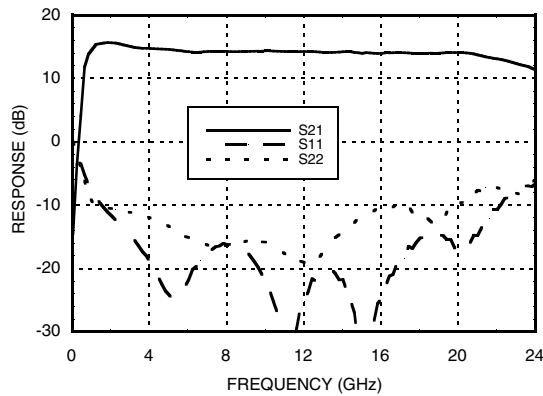


**GaAs PHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**

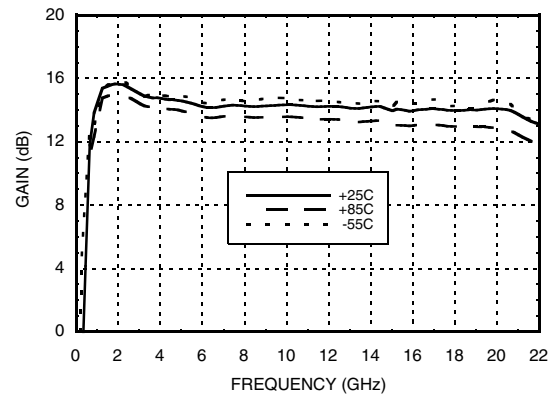
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AMPLIFIERS - LOW NOISE - CHIP

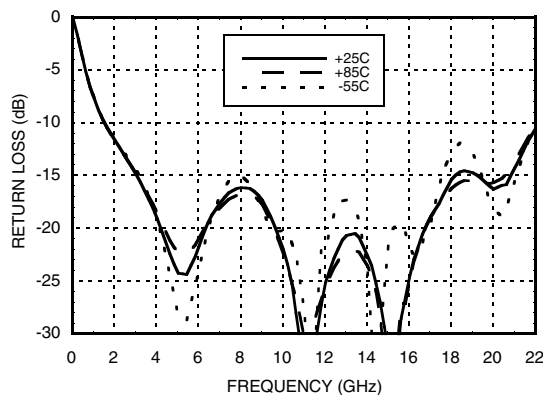
Gain & Return Loss



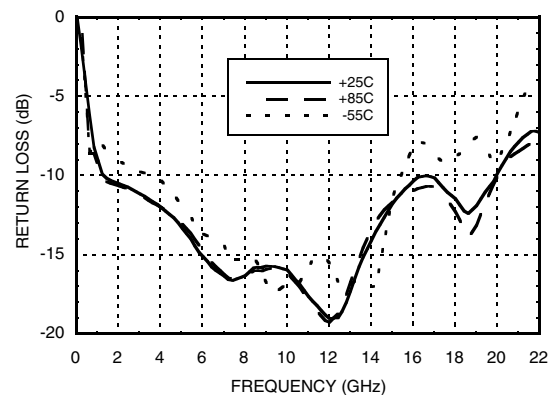
Gain vs. Temperature



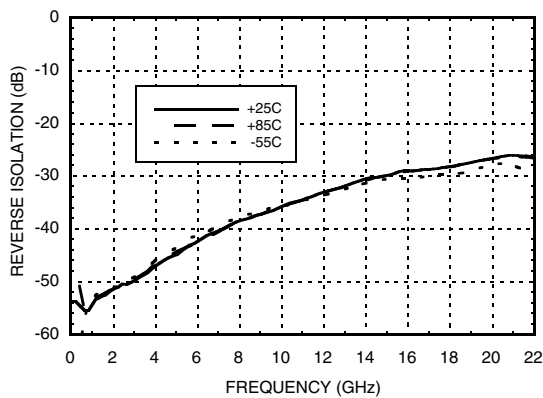
Input Return Loss vs. Temperature



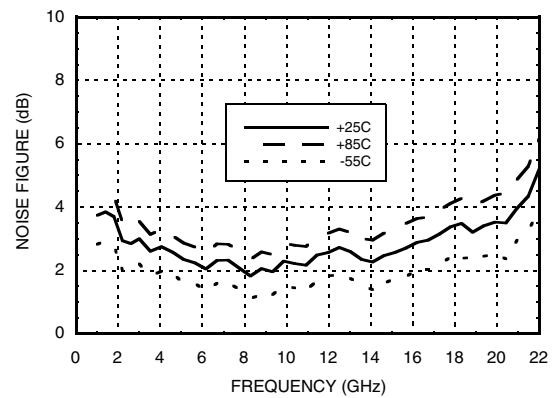
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature



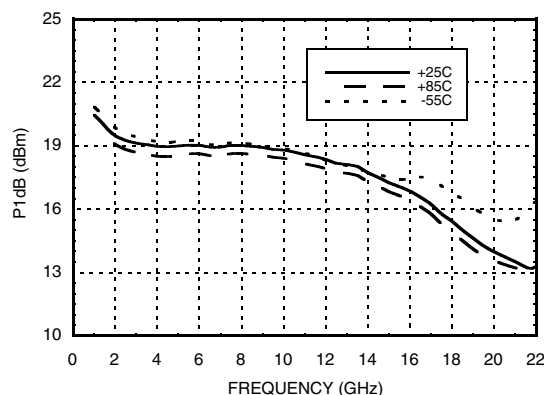
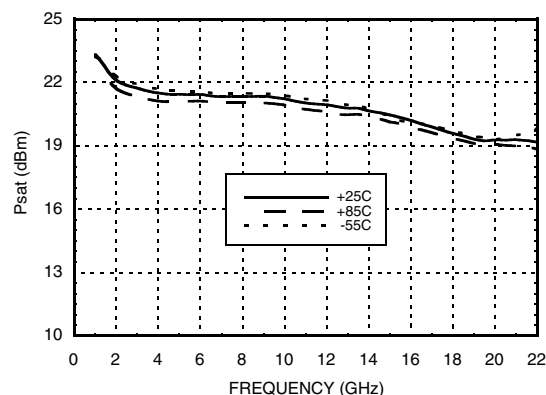
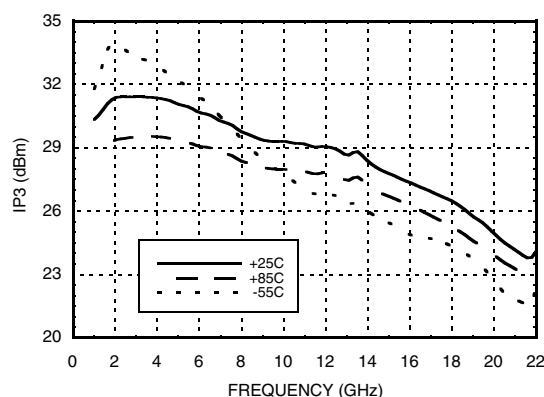
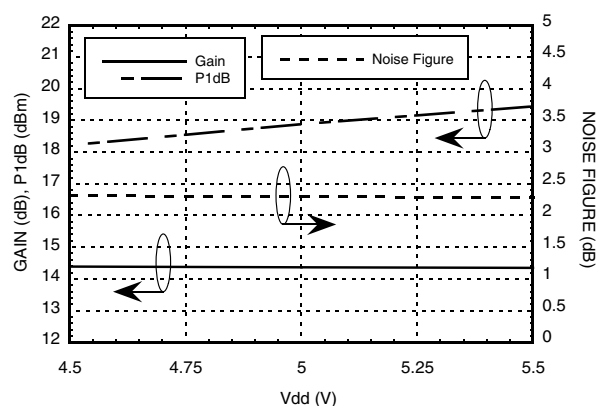
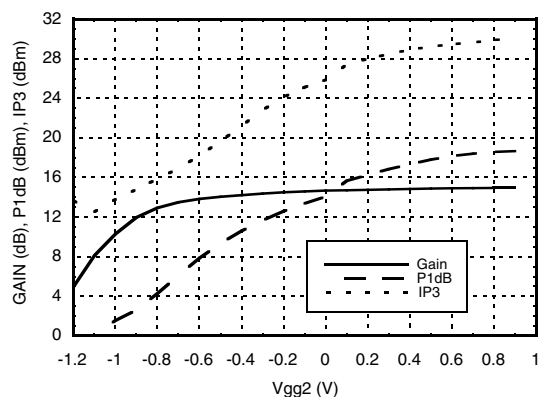
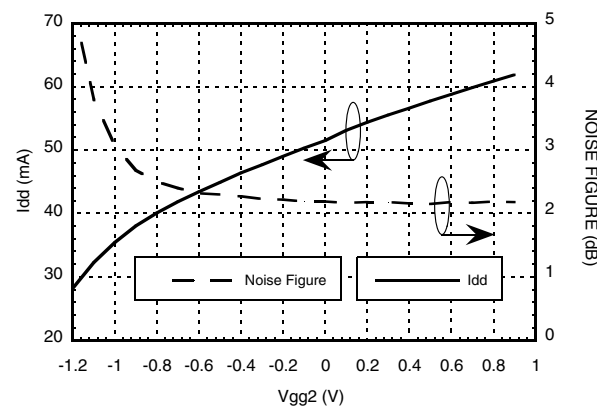
Noise Figure vs. Temperature



GaAs PHEMT MMIC LOW NOISE AGC AMPLIFIER, 2 - 20 GHz

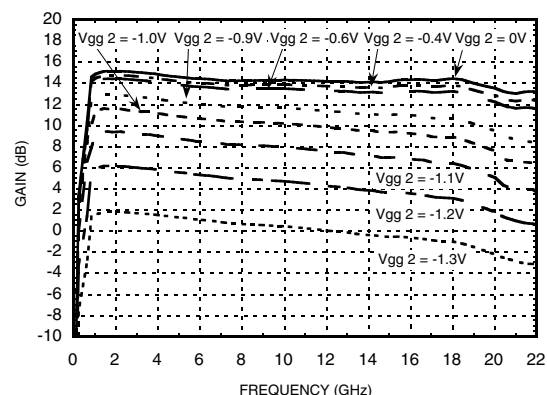
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AMPLIFIERS - LOW NOISE - CHIP

P1dB vs. Temperature

Psat vs. Temperature

Output IP3 vs. Temperature

**Gain, Power & Noise Figure
vs. Supply Voltage @ 10 GHz, Fixed Vgg1**

**Gain, P1dB & Output IP3
vs. Control Voltage @ 10 GHz**

**Noise Figure & Supply Current
vs. Control Voltage @ 10 GHz**


GaAs PHEMT MMIC LOW NOISE AGC AMPLIFIER, 2 - 20 GHz

Gain @ Several Control Voltages



Absolute Maximum Ratings

Drain Bias Voltage (V _{dd})	+9 V
Gate Bias Voltage (V _{gg1})	-2 to 0 V _{dc}
Gate Bias Current (I _{gg1})	2.5 mA
Gate Bias Voltage (V _{gg2})(AGC)	(V _{dd} -9) V _{dc} to +2 V _{dc}
RF Input Power (RFIN)(V _{dd} = +5 V)	+18 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T= 85 °C) (derate 20.6 mW/°C above 85 °C)	1.85 W
Thermal Resistance (channel to die bottom)	48.6 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C
ESD Sensitivity (HBM)	Class 0B - Passed 150V

Typical Supply Current vs. V_{dd}

V _{dd} (V)	I _{dd} (mA)
+4.5	58
+5.0	60
+5.5	62



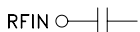
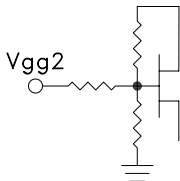
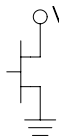
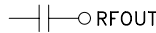
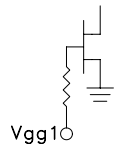

**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Standard	Alternate
GP-2 (Gel Pack)	[2]

[2] For alternate packaging information contact Analog Devices, Inc.

1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
2. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
3. DIE THICKNESS IS 0.004 (0.100)
4. TYPICAL BOND PAD IS 0.004 (0.100) SQUARE
5. BACKSIDE METALLIZATION: GOLD
6. BACKSIDE METAL IS GROUND
7. BOND PAD METALLIZATION: GOLD
8. OVERALL DIE SIZE $\pm .002"$

**GaAs PHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**
1
AMPLIFIERS - LOW NOISE - CHIP
Pad Descriptions

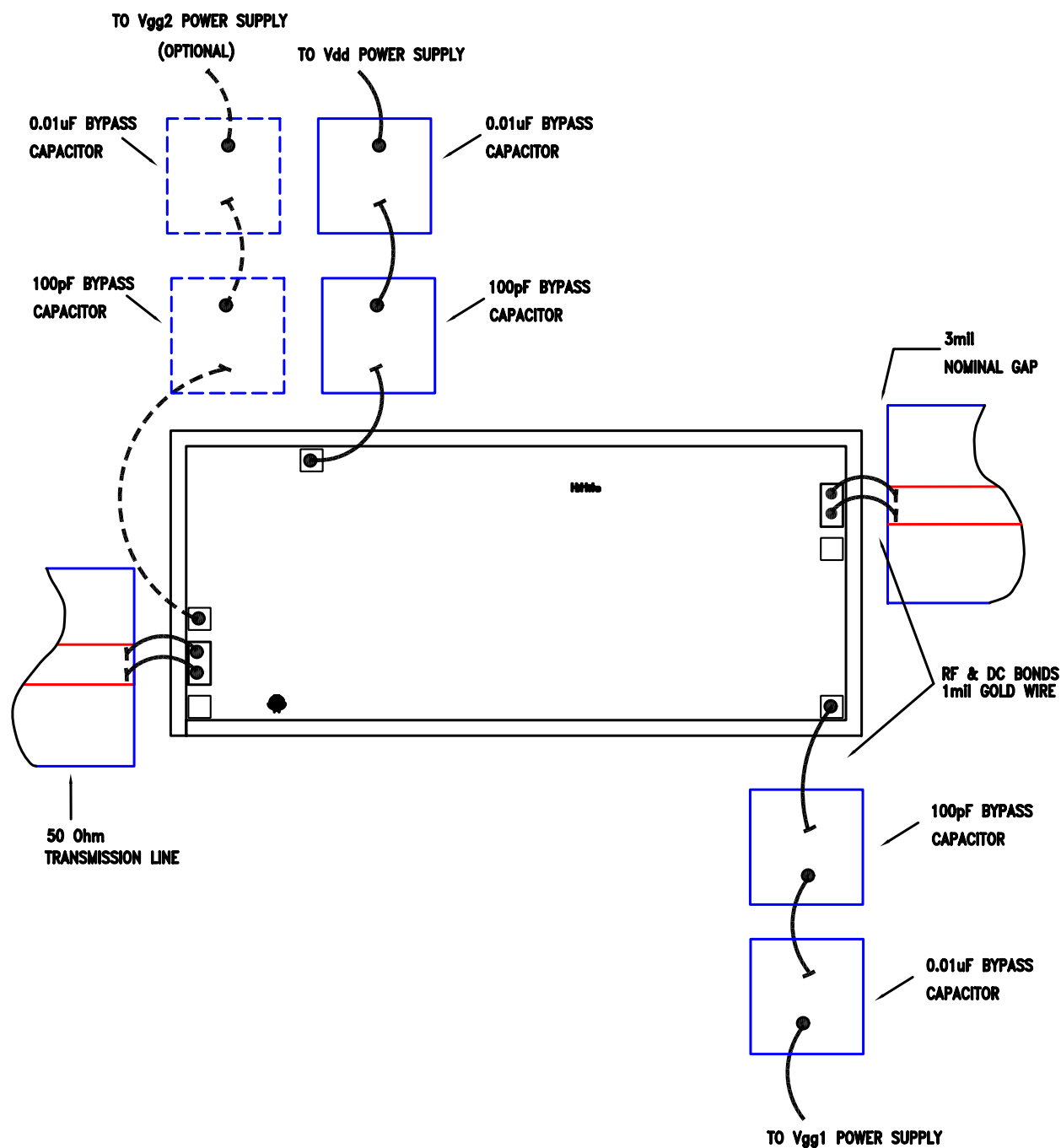
Pad Number	Function	Description	Interface Schematic
1	RFIN	This pad is AC coupled and matched to 50 Ohms.	
2	Vgg2	Optional gate control if AGC is required. Leave Vgg2 open circuited if AGC is not required.	
3	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required	
4	RFOUT	This pad is AC coupled and matched to 50 Ohms.	
5	Vgg1	Gate control for amplifier. Adjust to achieve Idd= 60 mA.	
Die Bottom	GND	Die bottom must be connected to RF/DC ground.	

**GaAs PHEMT MMIC LOW NOISE
AGC AMPLIFIER, 2 - 20 GHz**

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AMPLIFIERS - LOW NOISE - CHIP

Assembly Diagram



GaAs PHEMT MMIC LOW NOISE AGC AMPLIFIER, 2 - 20 GHz

1

AMPLIFIERS - LOW NOISE - CHIP

Mounting & Bonding Techniques for Millimeterwave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy (see HMC general Handling, Mounting, Bonding Note).

50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2).

Microstrip substrates should be brought as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm to 0.152 mm (3 to 6 mils).

Handling Precautions

Follow these precautions to avoid permanent damage.

Storage: All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

Static Sensitivity: Follow ESD precautions to protect against ESD strikes.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip has fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

Eutectic Die Attach: A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach: Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer's schedule.

Wire Bonding

Ball or wedge bond with 0.025mm (1 mil) diameter pure gold wire. Thermosonic wirebonding with a nominal stage temperature of 150 °C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds. Wirebonds should be started on the chip and terminated on the package or substrate. All bonds should be as short as possible <0.31mm (12 mils).

